Session Program

21–23 Jun 2021

The 38th RD50 Workshop (online Workshop)

Defect and Material Characterization - Acceptor removal studies

Monday 21 June

09:20

Defect and Material Characterization - Acceptor removal studies: Defect and Material Characterization - Acceptor removal studies

Session | **Convener:** Ioana Pintilie

09:20–09:40

Defects formed in boron-doped Si diodes after high energy electron irradiation

Speaker
Anja Himmerlich

09:40–10:00

Current Deep Level Transient Spectroscopy (I-DLTS) technique applied to p-type silicon diodes for Acceptor Removal studies

Speaker
Yana Gurimskaya

10:00–10:20

The boron-oxygen (BiOi) defect complex induced by irradiation with 6 MeV electrons in p-type silicon diodes

Speaker
Mr Chuan Liao

10:20–10:40

Bistability of the BiOi complex – a reason for the observed large scattering in the determined acceptor removal rates in irradiated p-type silicon

Speaker
Ioana Pintilie

10:40–10:50 **Coffee Break**

10:50–11:10

Modelling of the Coulombic centres charge emission: electric field approximation comparison in simulating the measured TSC signal

Speaker
Dr Lucian Filip

11:10–11:30

Investigation of acceptor removal by 4-point probe and LTPL measurements

Speaker
Kevin Lauer

11:30–11:50 **Optical detection of single defects in silicon**

Speaker
Dr Anaïs DREAU

11:50–12:10

Update on radiation damage investigation of epitaxial p-type Silicon using Schottky / pn junctions

Speaker
Christoph Thomas Klein

12:10–12:30
LGAD irradiated with 1e19 1MeV n/cm2 - HRTEM annealing studies up to 350 oC

Speaker
Dr Andrei Kuncser

12:30–13:00 **Discussion on defects and material characterization**

Speaker
Ioana Pintilie

13:00